

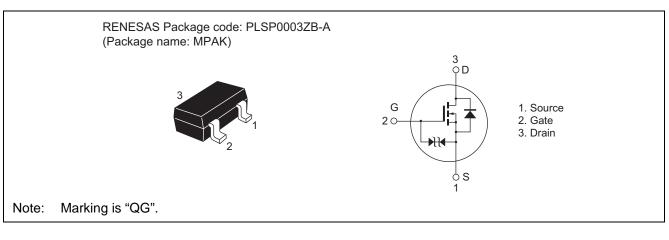
RQK0201QGDQA

Silicon N Channel MOS FET Power Switching

Features

- Low on-resistance
 - $R_{DS(on)} = 25 \text{ m}\Omega \text{ typ } (V_{GS} = 4.5 \text{ V}, I_D = 2.4 \text{ A})$
- Low drive current
- High speed switching
- 2.5 V gate drive

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
ltem	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	20	V
Gate to source voltage	V _{GSS}	±12	V
Drain current	ID	4.5	А
Drain peak current	I _{D(pulse)} Note1	15	А
Body - drain diode reverse drain current	I _{DR}	4.5	А
Channel dissipation	Pch Note2	0.8	W
Channel temperature	Tch	150	۵°
Storage temperature	Tstg	-55 to +150	۵°

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Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. When using the glass epoxy board (FR-4: 40 x 40 x 1 mm)



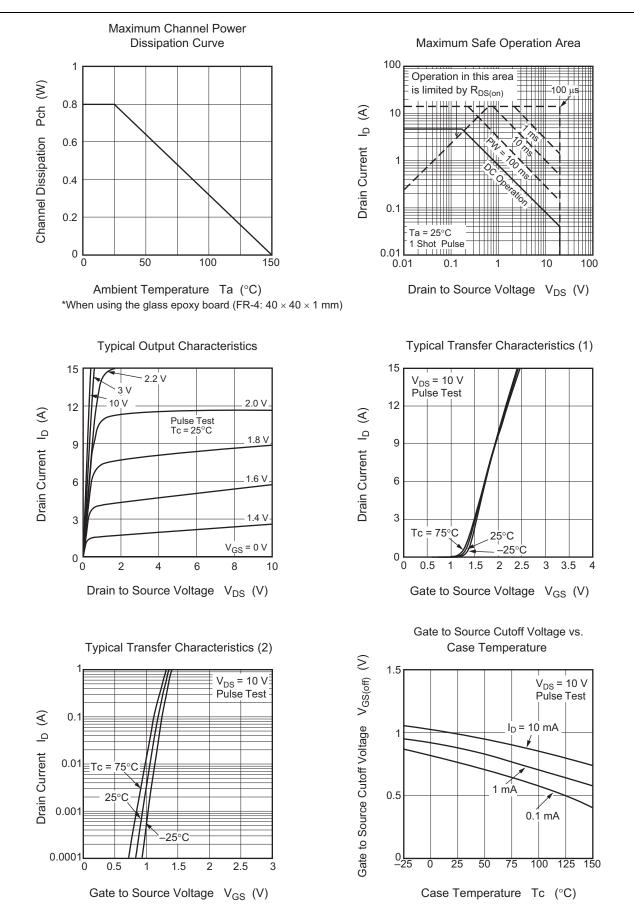
Electrical Characteristics

						$(Ta = 25^{\circ}C)$	
ltem	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	V _{(BR)DSS}	20	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	V _{(BR)GSS}	±12	—	—	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$	
Gate to source leak current	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	
Drain to source leak current	I _{DSS}	_	_	1	μA	$V_{DS} = 20 V, V_{GS} = 0$	
Gate to source cutoff voltage	V _{GS(off)}	0.4	_	1.4	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	
Drain to source on state resistance	R _{DS(on)}		30	39	mΩ	$I_D = 2.4A, V_{GS} = 4.5 V^{Note3}$	
	R _{DS(on)}		38	53	mΩ	$I_D = 2.4A, V_{GS} = 2.5 V^{Note3}$	
Forward transfer admittance	y _{fs}	9	12		S	$I_D = 2.4A, V_{DS} = 10 V^{Note3}$	
Input capacitance	Ciss		479	—	pF	V _{DS} = 10 V	
Output capacitance	Coss	_	106	—	pF	$V_{GS} = 0$	
Reverse transfer capacitance	Crss	_	48	—	pF	f = 1 MHz	
Turn - on delay time	t _{d(on)}	_	14	—	ns	I _D = 2.4 A	
Rise time	tr	_	53	—	ns	V _{GS} = 4.5 V	
Turn - off delay time	t _{d(off)}	_	35	—	ns	$R_L = 5.50 \Omega$	
Fall time	t _f	_	6	—	ns	Rg = 4.7 Ω	
Total gate charge	Qg	_	4.6	—	nC	V _{DD} = 10 V	
Gate to source charge	Qgs		0.9	_	nC	V _{GS} = 4.5 V	
Gate to drain charge	Qgd		1.3	_	nC	I _D = 4.5 A	
Body - drain diode forward voltage	V _{DF}	_	0.85	1.1	V	$I_F = 4.5 \text{ A}, V_{GS} = 0^{Note3}$	

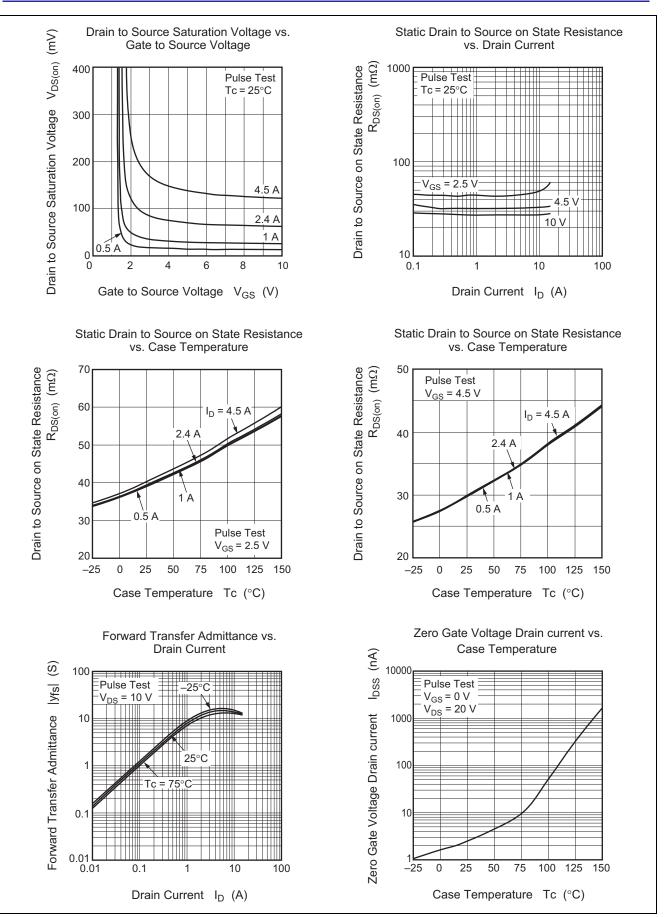
Notes: 3. Pulse test

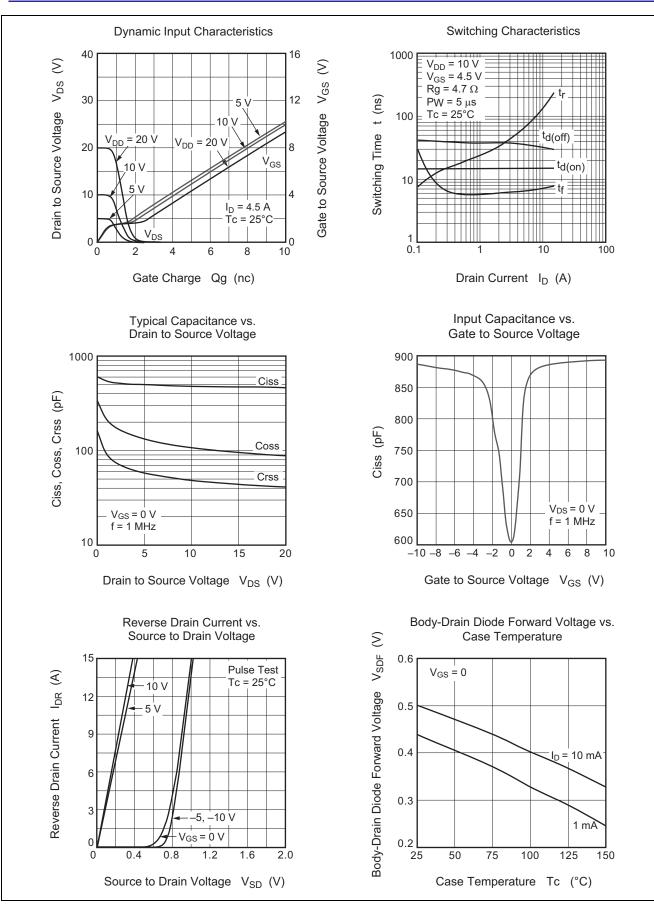


Main Characteristics



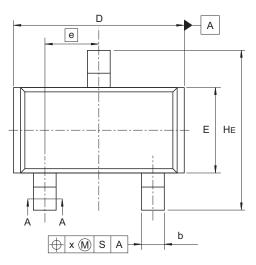


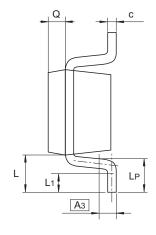


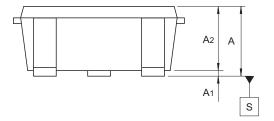


Package Dimensions

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
SC-59A	PLSP0003ZB-A	MPAK(T) / MPAK(T)V	0.011











Reference	Dimensions in millimeters		
Symbol	Min	Nom	Max
Α	1.0		1.3
A ₁	0		0.1
A ₂	1.0	1.1	1.2
A ₃		0.25	
b	0.35	0.4	0.5
С	0.1	0.16	0.26
D	2.7		3.1
E	1.35	1.5	1.65
е		0.95	
HE	2.2	2.8	3.0
L	0.35	—	0.75
L ₁	0.15		0.55
LP	0.25		0.65
Х			0.05
Q		0.3	

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Ordering Information

Orderable Part Number	Quantity	Shipping Container
RQK0201QGDQATL-H	3000 pcs.	φ178 mm reel, 8 mm Emboss taping



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